

#### **Features**

- · Split Gate Trench MOSFET technology
- · Excellent Package for Heat Dissipation
- High Density Cell Desihn for Low R<sub>DS(on)</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- · Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

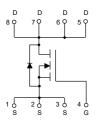
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 55°C/W Junction to Ambient(Note 2)
- Thermal Resistance: 1.2°C/W Junction to Case

| Parameter                                       | Symbol                | Rating           | Unit |    |
|---|-----------------------|------------------|------|----|
| Drain-Source Voltage                            |                       | V <sub>DS</sub>  | 60   | V  |
| Gate-Source Volltage                            |                       | V <sub>GS</sub>  | ±20  | V  |
| Drain Current                                   |                       | I <sub>D</sub>   | 130  | А  |
| Continuous Drain<br>Current <sup>(Note 3)</sup> | T <sub>C</sub> =25°C  | 1                | 85   | Α  |
|   | T <sub>C</sub> =100°C | - I <sub>D</sub> | 54   | А  |
| Pulsed Drain Current (Note 4)                   |                       | I <sub>DM</sub>  | 390  | Α  |
| Single Pulse Avalanche Energy (Note 5)          |                       | E <sub>AS</sub>  | 270  | mJ |
| Total Power Dissipation (Note 6)                |                       | P <sub>D</sub>   | 105  | W  |

#### Note:

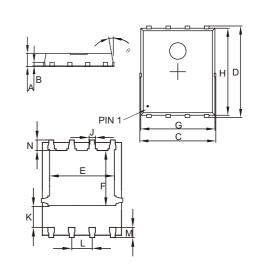
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- The Value of R<sub>BJA</sub> is Measured with the Device Mounted on 1 in<sup>2</sup> FR-4 Board with 2oz. Copper, in a Still Air Environment with T<sub>A</sub>=25°C.
- 3. The Maximum Current Rating is Package Limited.
- 4. Pulse Width Limited by Max. Junction Temperature.
- 5.  $V_{DD}$ =50 V,  $R_G$ =25  $\Omega$ , L=0.5mH, starting  $T_J$ =25°C.
- 6. PD is Based on Max. Junction Temperature, Using Junction-Case Thermal Resistance.

#### **Internal Structure**



# N-CHANNEL MOSFET

## **DFN5060**



| DIMENSIONS |       |        |       |      |      |
|------------|-------|--------|-------|------|------|
| DIM        | INC   | INCHES |       | M    | NOTE |
| וווט       | MIN   | MAX    | MIN   | MAX  | NOIL |
| Α          | 0.031 | 0.047  | 0.80  | 1.20 |      |
| В          | 0.010 |        | 0.254 |      | TYP. |
| С          | 0.193 | 0.222  | 4.90  | 5.64 |      |
| D          | 0.232 | 0.250  | 5.90  | 6.35 |      |
| E          | 0.148 | 0.167  | 3.75  | 4.25 |      |
| F          | 0.126 | 0.154  | 3.20  | 3.92 |      |
| G          | 0.189 | 0.213  | 4.80  | 5.40 |      |
| Н          | 0.222 | 0.239  | 5.65  | 6.06 |      |
| K          | 0.045 | 0.059  | 1.15  | 1.50 |      |
| J          | 0.012 | 0.020  | 0.30  | 0.50 |      |
| L          | 0.046 | 0.054  | 1.17  | 1.37 |      |
| М          | 0.012 | 0.028  | 0.30  | 0.71 |      |
| N          | 0.016 | 0.028  | 0.40  | 0.71 |      |



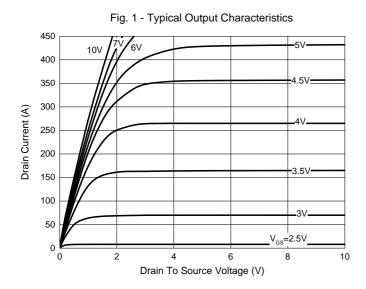
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

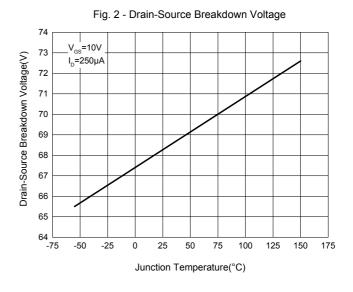
| Parameter                                  | Symbol               | Test Conditions   | Min | Тур  | Max  | Unit |  |
|--|----------------------|---|-----|------|------|------|--|
| Static Characteristics                     |                      |   |     |      |      |      |  |
| Drain-Source Breakdown Voltage             | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                    | 60  |      |      | V    |  |
| Gate-Source Leakage Current                | I <sub>GSS</sub>     | $V_{DS}=0V, V_{GS}=\pm 20V$                                   |     |      | ±100 | nA   |  |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>     | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                     |     |      | 1    | μΑ   |  |
| Gate-Threshold Voltage                     | V <sub>GS(th)</sub>  | $V_{DS}=V_{GS}$ , $I_{D}=250\mu A$                            | 1   | 1.8  | 2.5  | V    |  |
| Drain-Source On-Resistance                 | В                    | V <sub>GS</sub> =10V, I <sub>D</sub> =20A                     |     | 2.5  | 3    |      |  |
|  | R <sub>DS(on)</sub>  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A                    |     | 3.5  | 4.5  | - mΩ |  |
| Diode Forward Voltage                      | V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =20A                      |     |      | 1.2  | V    |  |
| Continuous Body Diode Current              | I <sub>S</sub>       |   |     |      | 85   | Α    |  |
| Dynamic Characteristics <sup>(Note 7</sup> | )                    |   |     |      |      |      |  |
| Input Capacitance                          | C <sub>iss</sub>     |   |     | 3350 |      | pF   |  |
| Output Capacitance                         | C <sub>oss</sub>     | V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,f=1MHz               |     | 1666 |      |      |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>     |   |     | 77.7 |      |      |  |
| Total Gate Charge                          | $Q_g$                |   |     | 66.1 |      |      |  |
| Gate-Source Charge                         | Q <sub>gs</sub>      | V <sub>DS</sub> =30V,V <sub>GS</sub> =10V,I <sub>D</sub> =25A |     | 10.7 |      | 20   |  |
| Gate-Drain Charge                          | $Q_{gd}$             |   |     | 10.9 |      | nC   |  |
| Reverse Recovery Chrage                    | Q <sub>rr</sub>      | I <sub>S</sub> =25A, di/dt=100A/μs                            |     | 73   |      |      |  |
| Reverse Recovery Time                      | t <sub>rr</sub>      | 1 <sub>S</sub> =25A, αι/αι=100A/μS                            |     | 68   |      |      |  |
| Turn-On Delay Time                         | t <sub>d(on)</sub>   |   |     | 22.5 |      |      |  |
| Turn-On Rise Time                          | t <sub>r</sub>       | V <sub>GS</sub> =10V,V <sub>DD</sub> =30V,I <sub>D</sub> =25A |     | 6.7  |      | ns   |  |
| Turn-Off Delay Time                        | t <sub>d(off)</sub>  | R <sub>GEN</sub> =2Ω  |     | 80.3 |      |      |  |
| Turn-Off Fall Time                         | t <sub>f</sub>       |   |     | 26.9 |      |      |  |

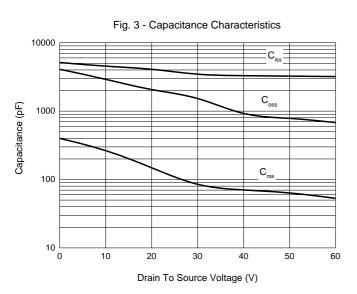
Note 7. Guaranteed by Design, Not Subject to Production Testing.

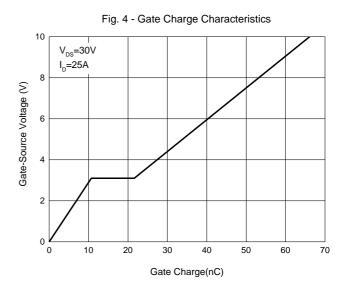


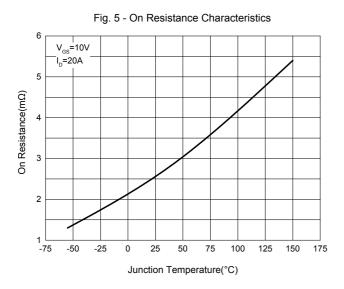
#### **Curve Characteristics**

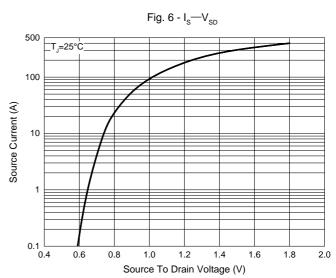














### **Ordering Information**

| Device         | Packing               |  |
|----------------|-----------------------|--|
| Part Number-TP | Tape&Reel: 5Kpcs/Reel |  |

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